

isc N-Channel MOSFET Transistor

2SK557

DESCRIPTION

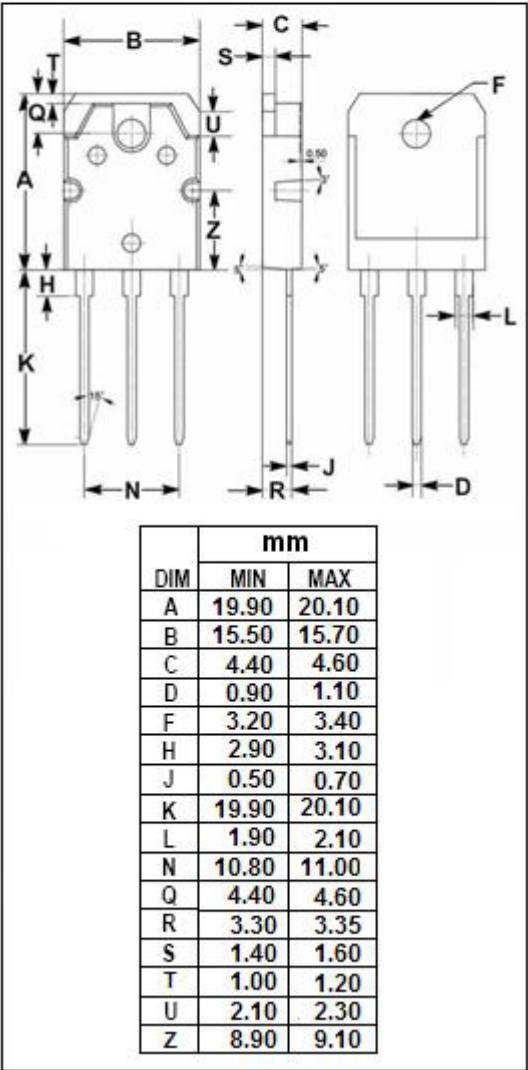
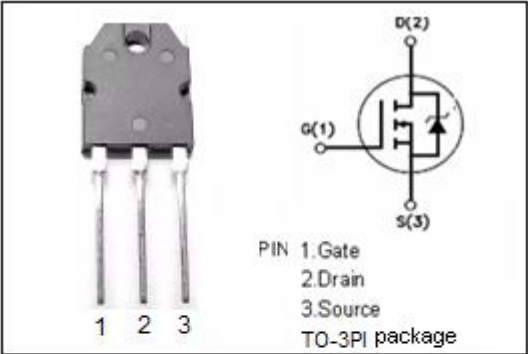
Drain Current $I_D=12A@T_C=25!$
Drain Source Voltage-
: $V_{DSS}=500V(\text{Min})$
Fast Switching Speed

APPLICATIONS

Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	" 20	V
I_D	Drain Current-continuous@ $TC=25!$	12	A
P_{tot}	Total Dissipation@ $TC=25!$	100	W
T_j	Max. Operating Junction Temperature	150	!
T_{stg}	Storage Temperature Range	-55~150	!



isc N-Channel Mosfet Transistor

2SK557

! ELECTRICAL CHARACTERISTICS (T_c=25)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	500			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = 10V; I _D = 1mA	2.0		4.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =6A		0.45	0.60	#
V _{SD}	Diode Forward Voltage	I _F = 12A; V _{GS} =0		1.0		V
I _{GSS}	Gate Source Leakage Current	V _{GS} = " 16V; V _{DS} = 0			" 10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =400V; V _{GS} = 0			250	uA
tr	Rise time	VGS=10V;ID=6A; RL=5#		85		ns
ton	Turn-on time			110		ns
tf	Fall time			85		ns
toff	Turn-off time			230		ns